A NOVEL METHOD OF DUAL GATE PROCESS

ABSTRACT

A new method for forming dual gate dielectrics having high quality where both thin and thick gate dielectric thicknesses can be controlled separately is described. An isolation region separates a first active area from a second active area in a semiconductor substrate. A first gate dielectric layer is formed overlying the semiconductor substrate in the first and second active areas wherein the first gate dielectric layer has a first electrical thickness. The first gate dielectric layer in the second active area is removed. A second gate dielectric layer is formed in the second active area wherein the second gate dielectric layer has a second electrical thickness greater than the first electrical thickness and wherein the second gate dielectric layer is nitrided. A polysilicon layer is deposited overlying the first and second gate dieectric layers. The layers are patterned to form a first gate transistor in the first active area having the first gate dielectric layer thereunder and to form a second gate transistor in the second active area having the second gate dielectric layer thereunder.

(Figure 1)